


Resonant Mode Combi IGBT®

The POWER MOS 7® IGBT used in this resonant mode combi is a new generation of high voltage power IGBTs. Using Punch Through Technology this IGBT is ideal for many high frequency, high voltage switching applications and has been optimized for high frequency switchmode power supplies.

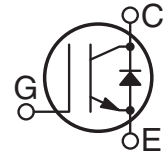
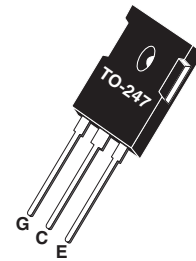
Features

- Low Conduction Loss
- Low Gate Charge
- Ultrafast Tail Current shutoff
- Low forward Diode Voltage (V_F)
- Ultrasoft Recovery Diode

- SSOA Rated
- RoHS Compliant 

Typical Applications

- Induction Heating
- Welding
- Medical
- High Power Telecom
- Resonant Mode Phase Shifted Bridge




MAXIMUM RATINGS

 All Ratings: $T_C = 25^\circ C$ unless otherwise specified.

Symbol	Parameter	Ratings	UNIT
V_{CES}	Collector-Emitter Voltage	600	Volts
V_{GE}	Gate-Emitter Voltage	± 20	
V_{GEM}	Gate-Emitter Voltage Transient	± 30	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ C$	56	Amps
I_{C2}	Continuous Collector Current @ $T_C = 110^\circ C$	27	
I_{CM}	Pulsed Collector Current ^① @ $T_C = 25^\circ C$	65	
SSOA	Switching Safe Operating Area @ $T_J = 150^\circ C$	65A @ 600V	
P_D	Total Power Dissipation	250	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ C$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{CES}	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 1.0mA$)	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 1mA, T_J = 25^\circ C$)	3	4.5	6	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 15A, T_J = 25^\circ C$)		2.2	2.7	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 15A, T_J = 125^\circ C$)		2.1		
I_{CES}	Collector Cut-off Current ($V_{CE} = 600V, V_{GE} = 0V, T_J = 25^\circ C$) ^②			275	μA
	Collector Cut-off Current ($V_{CE} = 600V, V_{GE} = 0V, T_J = 125^\circ C$) ^②			2750	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			± 100	nA

 CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT15GP60BDL(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1\text{ MHz}$		1685		pF	
C_{oes}	Output Capacitance			210			
C_{res}	Reverse Transfer Capacitance			15			
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 15A$		7.5		V	
Q_g	Total Gate Charge ^③			55		nC	
Q_{ge}	Gate-Emitter Charge			12			
Q_{gc}	Gate-Collector ("Miller") Charge			15			
SSOA	Switching Safe Operating Area	$T_J = 150^\circ C, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu H, V_{CE} = 600V$	65			A	
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 15A$ $R_G = 5\Omega$ $T_J = +25^\circ C$		8		ns	
t_r	Current Rise Time			12			
$t_{d(off)}$	Turn-off Delay Time			29			
t_f	Current Fall Time			58			
E_{on1}	Turn-on Switching Energy ^④				130		μJ
E_{on2}	Turn-on Switching Energy (With Diode) ^⑤				152		
E_{off}	Turn-off Switching Energy ^⑥				121		
$t_{d(on)}$	Turn-on Delay Time		Inductive Switching (125°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 15A$ $R_G = 5\Omega$ $T_J = +125^\circ C$		8		ns
t_r	Current Rise Time			12			
$t_{d(off)}$	Turn-off Delay Time			69			
t_f	Current Fall Time			88			
E_{on1}	Turn-on Switching Energy ^④				130		μJ
E_{on2}	Turn-on Switching Energy (With Diode) ^⑤				267		
E_{off}	Turn-off Switching Energy ^⑥				268		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.50	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			1.00	
W_T	Package Weight			5.90	gm

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② For Combi devices, I_{ces} includes both IGBT and diode leakages
- ③ See MIL-STD-750 Method 3471.
- ④ E_{on1} is the clamped inductive turn-on-energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. (See Figure 24.)
- ⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. A Combi device is used for the clamping diode as shown in the E_{on2} test circuit. (See Figures 21, 22.)
- ⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT15GP60BDL(G)

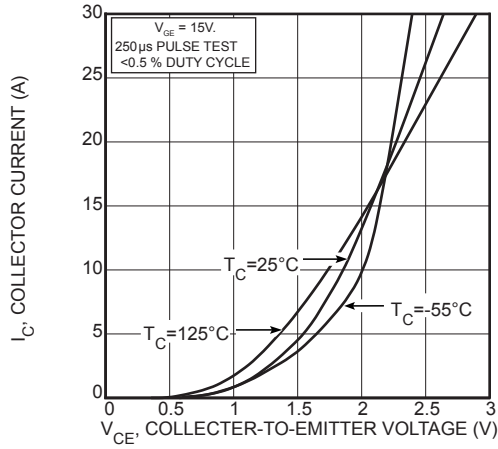


FIGURE 1, Output Characteristics ($V_{GE} = 15V$)

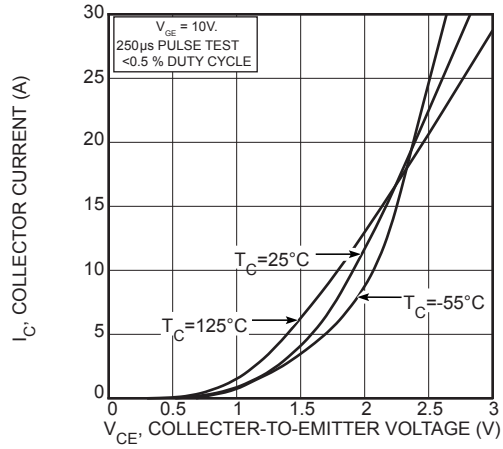


FIGURE 2, Output Characteristics ($V_{GE} = 10V$)

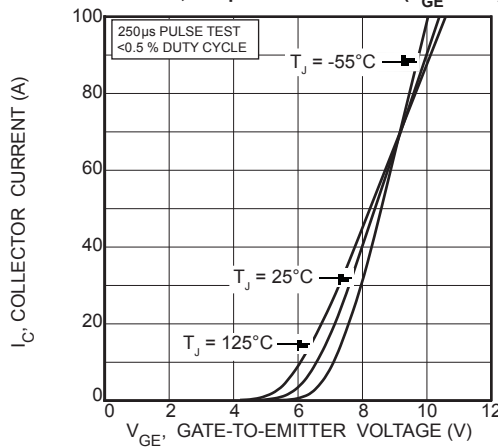


FIGURE 3, Transfer Characteristics

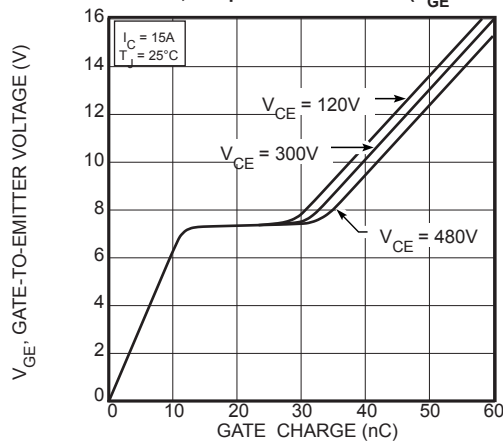


FIGURE 4, Gate Charge

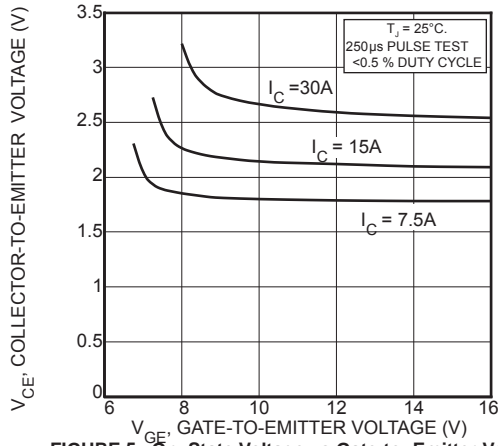


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

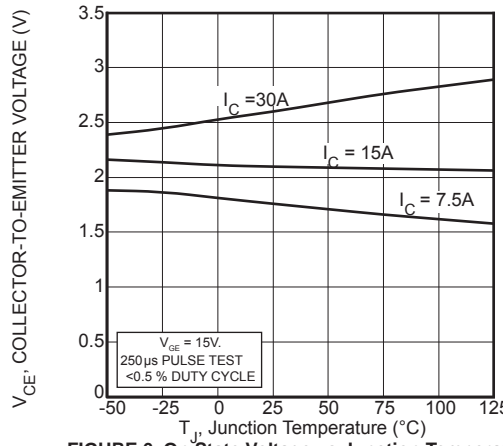


FIGURE 6, On State Voltage vs Junction Temperature

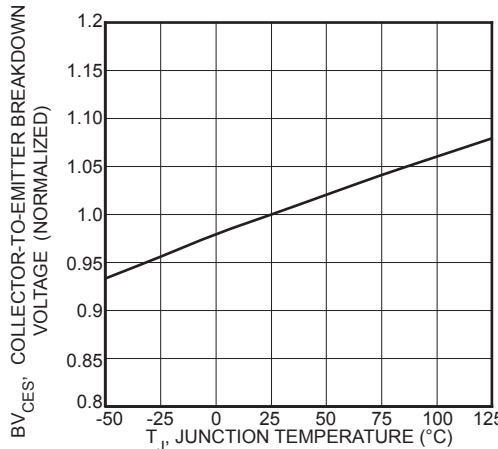


FIGURE 7, Breakdown Voltage vs. Junction Temperature

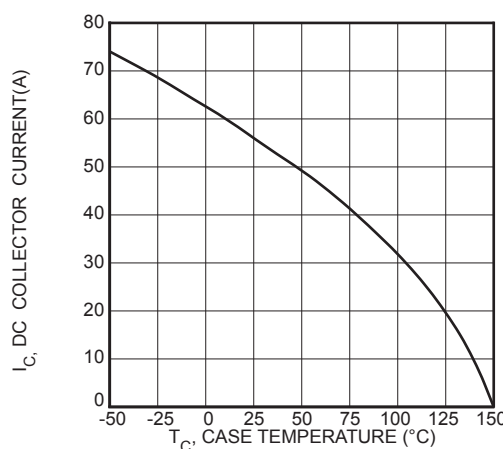


FIGURE 8, DC Collector Current vs Case Temperature

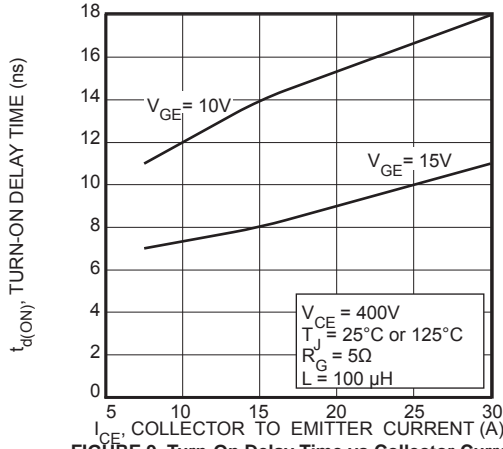


FIGURE 9, Turn-On Delay Time vs Collector Current

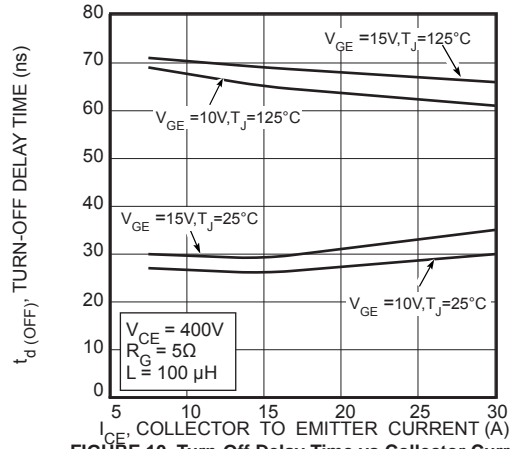


FIGURE 10, Turn-Off Delay Time vs Collector Current

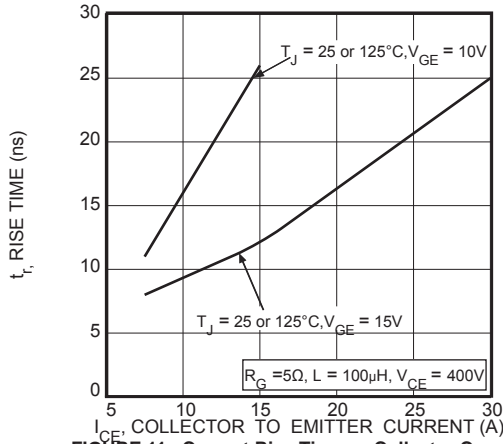


FIGURE 11, Current Rise Time vs Collector Current

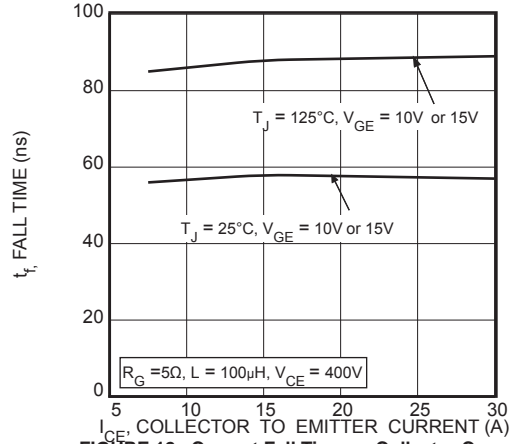


FIGURE 12, Current Fall Time vs Collector Current

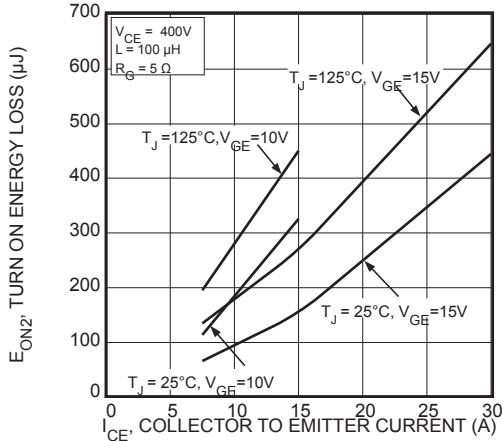


FIGURE 13, Turn-On Energy Loss vs Collector Current

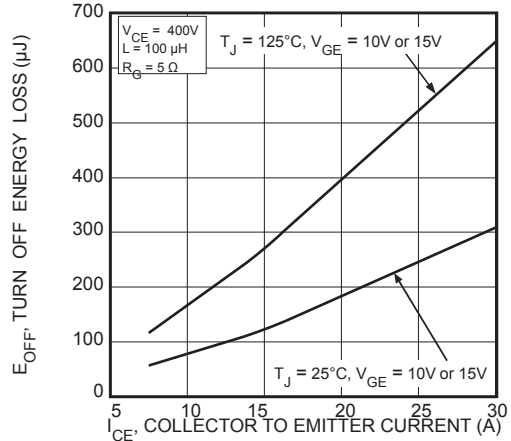


FIGURE 14, Turn Off Energy Loss vs Collector Current

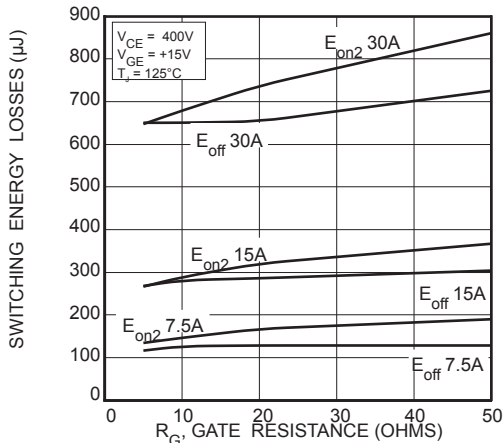


FIGURE 15, Switching Energy Losses vs. Gate Resistance

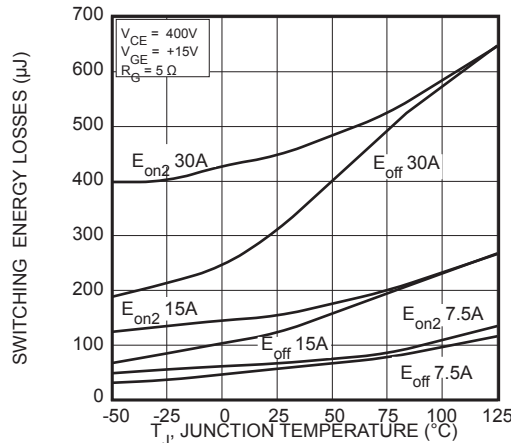


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

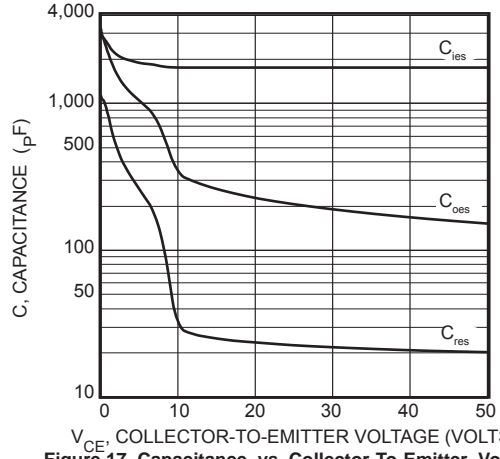


Figure 17, Capacitance vs Collector-To-Emitter Voltage

APT15GP60BDL(G)

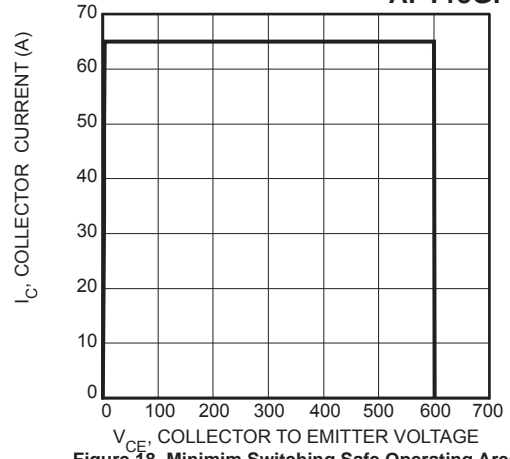


Figure 18, Minimum Switching Safe Operating Area

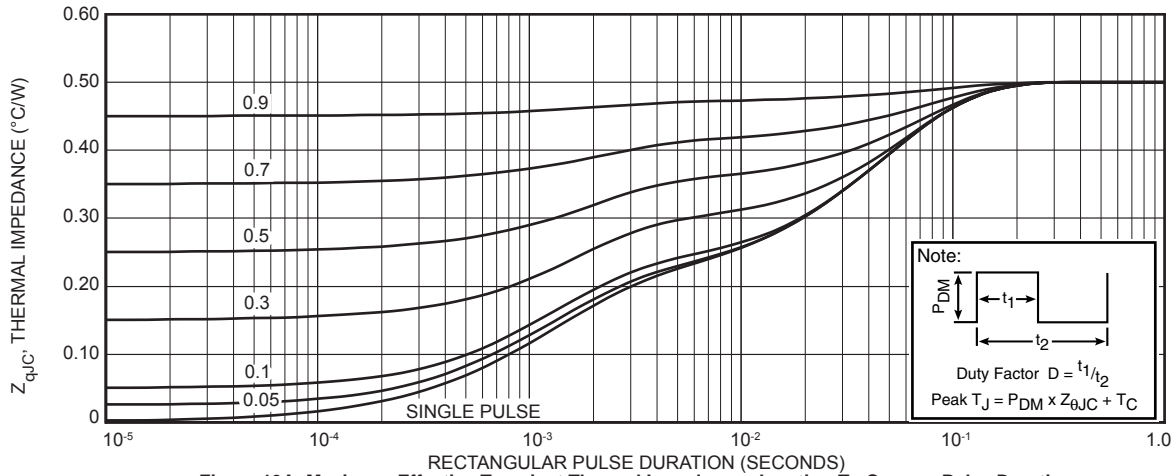


Figure 19A, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

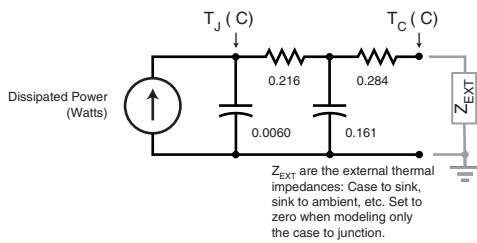


FIGURE 19B, TRANSIENT THERMAL IMPEDANCE MODEL

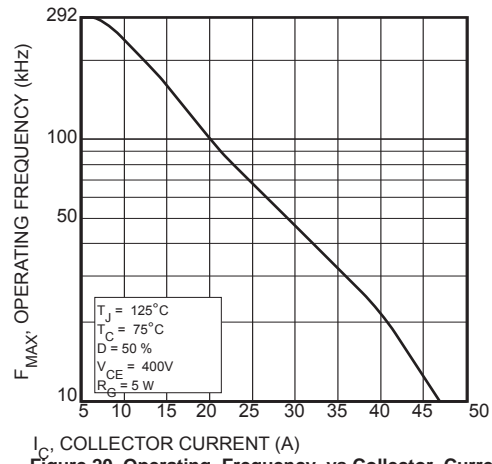


Figure 20, Operating Frequency vs Collector Current

$$F_{max} = \min(f_{max1}, f_{max2})$$

$$f_{max1} = \frac{0.05}{t_{d(on)} + t_r + t_{d(off)} + t_f}$$

$$f_{max2} = \frac{P_{diss} - P_{cond}}{E_{on2} + E_{off}}$$

$$P_{diss} = \frac{T_J - T_C}{R_{\theta JC}}$$

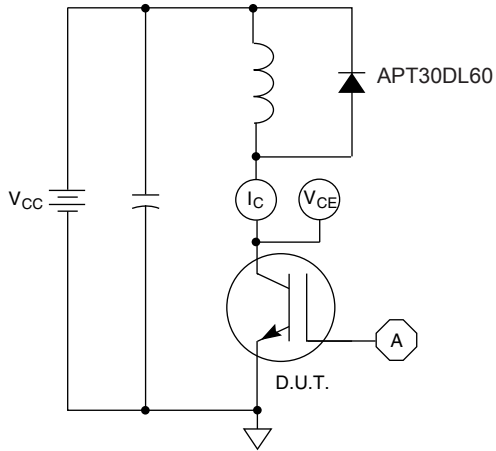


Figure 21, Inductive Switching Test Circuit

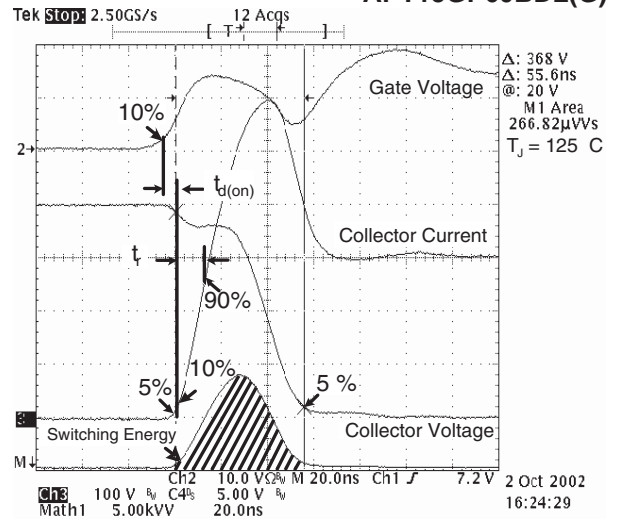


Figure 22, Turn-on Switching Waveforms and Definitions

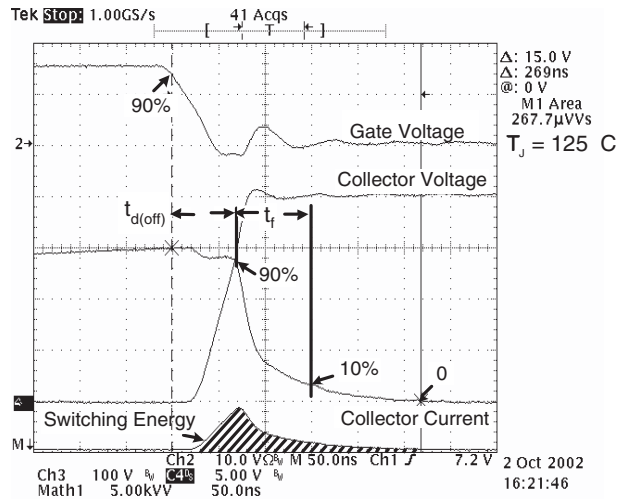


Figure 23, Turn-off Switching Waveforms and Definitions

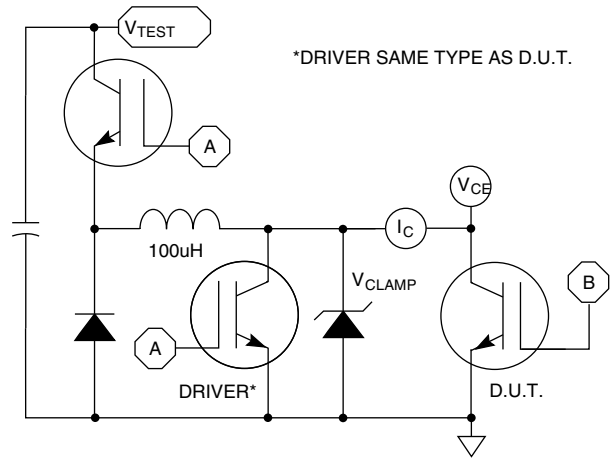


Figure 24, E_{ON1} Test Circuit

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT15GP60BDL(G)		UNIT
$I_F(AV)$	Maximum Average Forward Current ($T_C = 126^\circ\text{C}$, Duty Cycle = 0.5)	30		Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)	51		
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)	320		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = 30\text{A}$	1.25	1.6	Volts
		$I_F = 60\text{A}$	2.0		
		$I_F = 30\text{A}, T_J = 125^\circ\text{C}$	1.25		

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	64		ns
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 25^\circ\text{C}$	-	317		
Q_{rr}	Reverse Recovery Charge		-	962		nC
I_{RRM}	Maximum Reverse Recovery Current		-	7	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	561		ns
Q_{rr}	Reverse Recovery Charge		-	2244		nC
I_{RRM}	Maximum Reverse Recovery Current		-	9	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	264		ns
Q_{rr}	Reverse Recovery Charge		-	3191		nC
I_{RRM}	Maximum Reverse Recovery Current		-	26		Amps

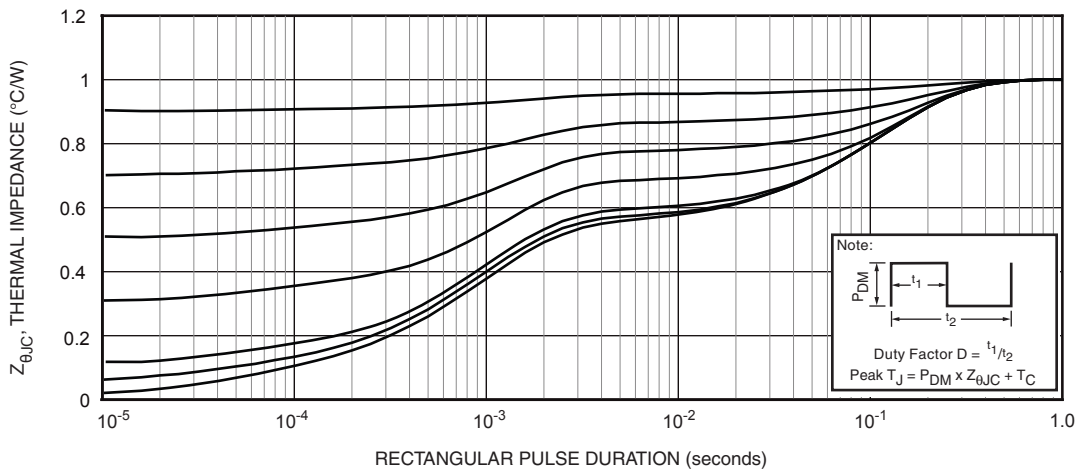


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

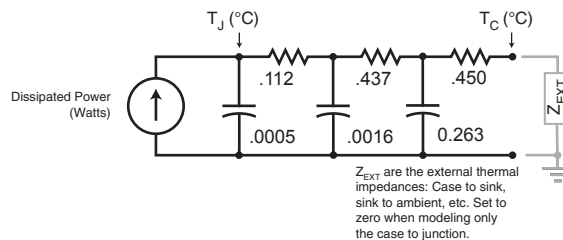


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

TYPICAL PERFORMANCE CURVES

APT15GP60BDL(G)

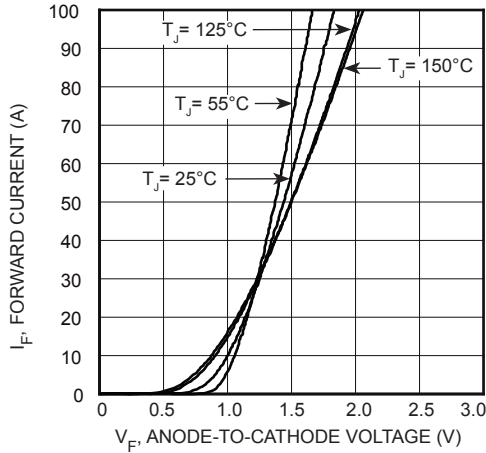


FIGURE 2, Forward Current vs. Forward Voltage

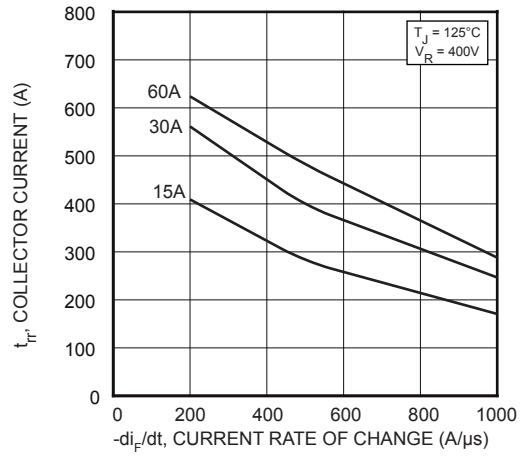


FIGURE 3, Reverse Recovery Time vs. Current Rate of Change

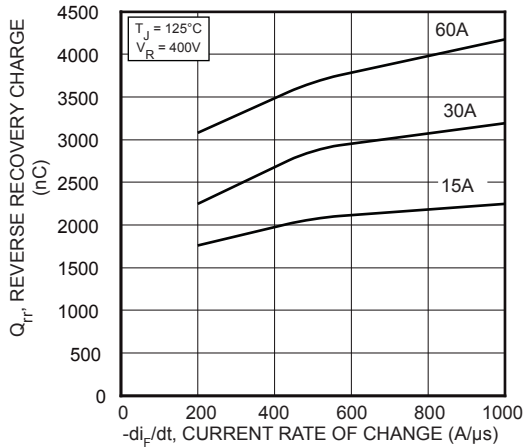


FIGURE 4, Reverse Recovery Charge vs. Current Rate of Change

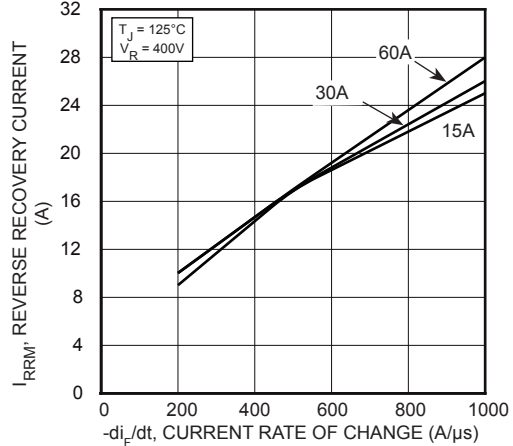


FIGURE 5, Reverse Recovery Current vs. Current Rate of Change

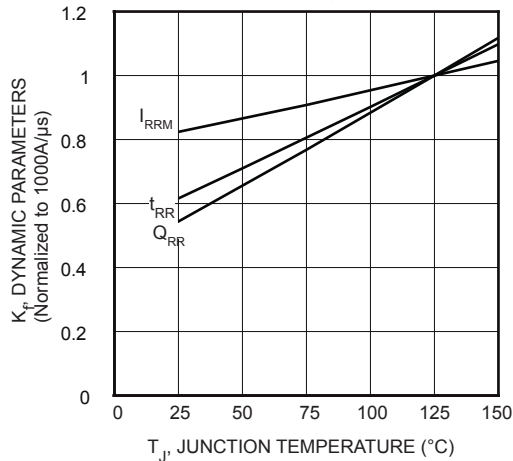


FIGURE 6, Dynamic Parameters vs. Junction Temperature

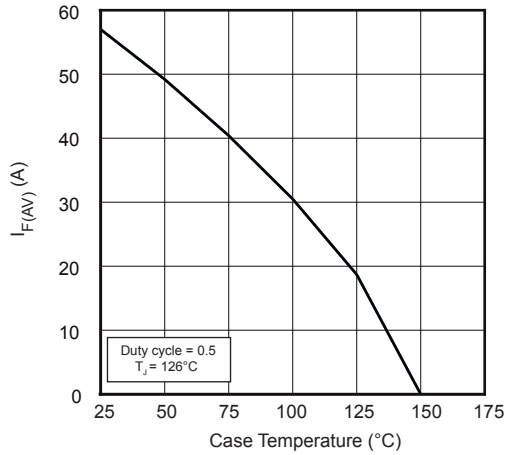


FIGURE 7, Maximum Average Forward Current vs. Case Temperature

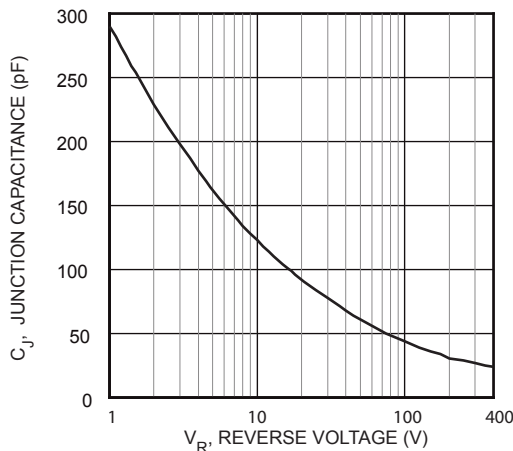


FIGURE 8, Junction Capacitance vs. Reverse Voltage

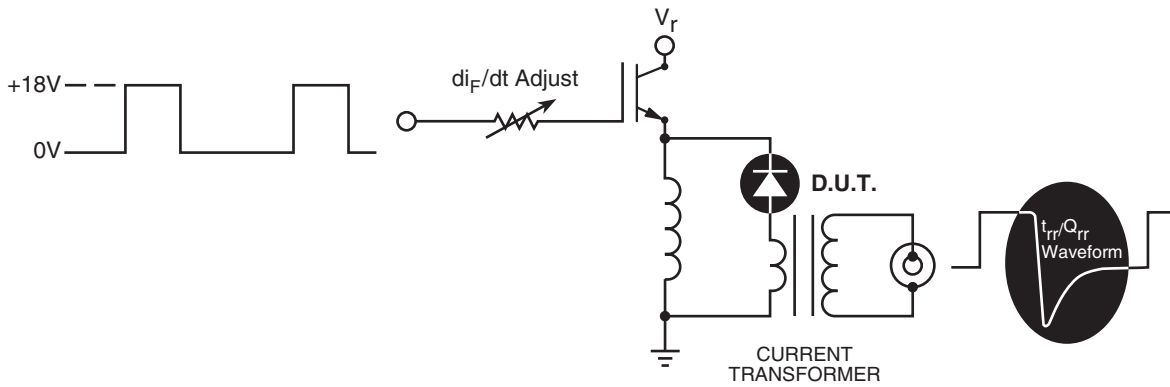


Figure 9. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .
- 6 di_M/dt - Maximum Rate of Current Increase During the Trailing Portion of t_{rr} .

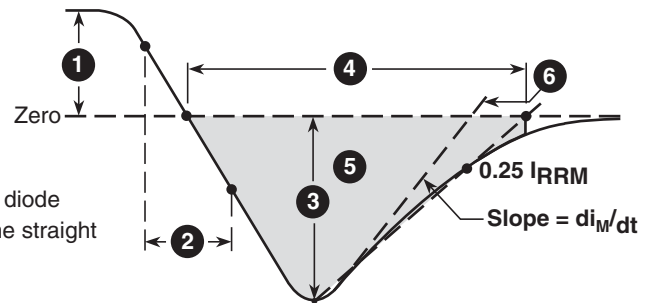
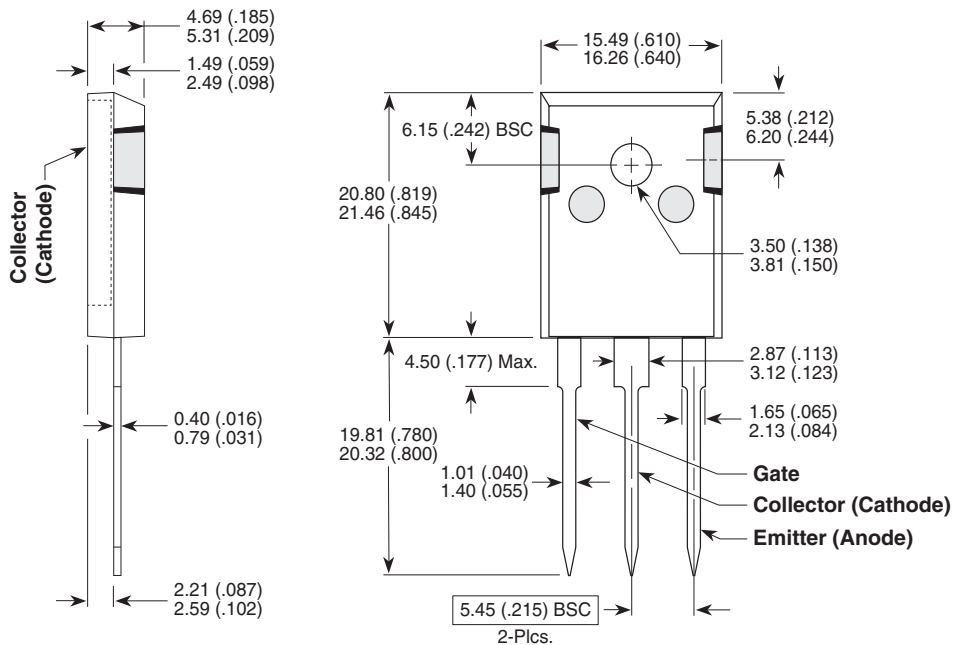


Figure 10, Diode Reverse Recovery Waveform and Definitions

TO-247 (B) Package Outline



Dimensions in Millimeters and (Inches)



Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

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